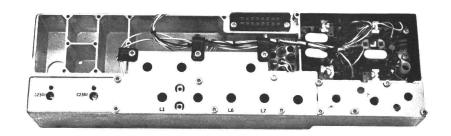
MASTR PROGRESS LINE

33-50 MHz DUAL FRONT END MODELS 19D413530-G3&G4



SPECIFICATIONS *

DUAL FRONT END 19D413530G3: 33-42 MHz

DUAL FRONT END 19D413530G4: 42-50 MHz

FREQUENCY RANGE 33-50 MHz

SENSITIVITY (DFE & RECEIVER)

12-dB SINAD 0.5 μ V 20-dB Quieting 0.6 μ V

INTERMODULATION (EIA) -75 dB

INPUT POWER .010 Amps at 10 volts

FREQUENCY STABILITY .0005% (-30° C to $+60^{\circ}$ C)

TRANSISTORS

DIMENSIONS (HxWxD) 2-1/4" x 11-3/4" x 4-3/8"

OPTIONS

7351: 1-Freq. Standard 7352: 2-Freq. Standard 7353: 3-Freq. Standard

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

TABLE OF CONTENTS

SPECIFICATIONS	Cover
DESCRIPTION	1
Antenna System	1
CIRCUIT ANALYSIS	2
RF Amplifier Oscillator/Multiplier Multiplier-Selectivity lst. Mixer	2 2 3 3
RECEIVER MODIFICATIONS	3
MAINTENANCE	3
Disassembly Test Procedures	3 4 5
OUTLINE DIAGRAM	ϵ
SCHEMATIC DIAGRAM	7
PARTS LIST AND PRODUCTION CHANGES	8
ILLUSTRATIONS	
Figure 1 - Dual Front End Block Diagram	1 2 3

DESCRIPTION

General Electric Dual Front End Models 19D413530-G3 & G4 were designed for operation in the 33 to 50 megahertz band. The Dual Front End (DFE) is used with MASTR Progress Line Receivers to monitor up to four frequencies when the channel spacing is greater than 0.4% ($\pm.2\%$). The standard DFE can also be used with 150.8-174 MHz receivers for cross-band application.

The DFE is of single-unit construction, completely housed in an aluminum casting for maximum shielding and rigidity. The standard unit consists of two helical resonators,

lst mixer, oscillator and two multiplier stages, and a high IF amplifier.

The chassis is mounted in a housing on the rear of the mobile frame, adding approximately three inches to the overall length of the mobile unit. A block diagram of the DFE is shown in Figure 1.

ANTENNA SYSTEM

The Dual Front End and the receiver use a common antenna. A power splitter mounted on the front of the system frame provides approximately 20-dB separation for the two to four receive channels. Due to

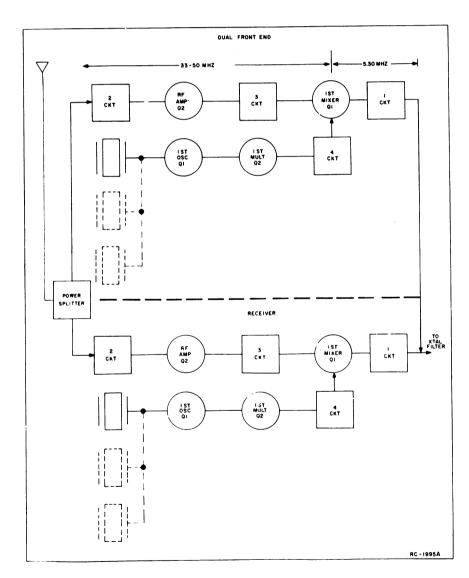


Figure 1 - Dual Front End Block Diagram

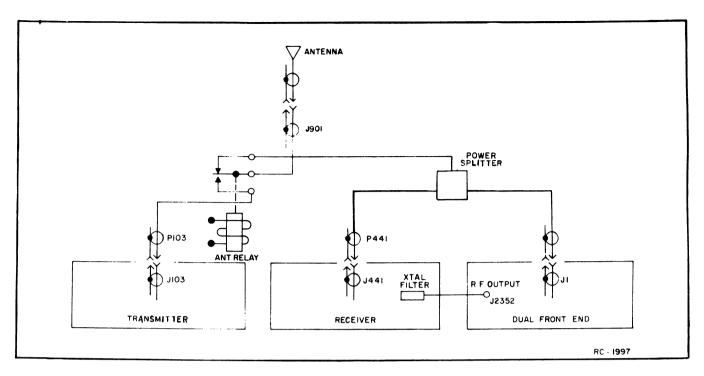


Figure 2 - Single Antenna Block Diagram

the isolation provided by the power splitter, cable lengths to the DFE and the receiver are not critical.

In standard applications, the antenna connects to J901 on the front of the mobile unit. From J901, the antenna connects to the common terminal of the antenna relay (see Figure 2). The transmitter connects to the normally-open contact on the antenna relay, while the normally-closed contact is connected to input jack J3 on the power splitter.

One cable from the power splitter connects to DFE input jack Jl, and the other cable connects to J441 on the receiver.

CIRCUIT ANALYSIS

The MASTR Progress Line Dual Front End is completely transistorized, using four silicon transistors. A regulated 10 volts is used for all stages of the Dual Front End.

Centralized metering jack J2351 is provided for use with GE Test Set Models 4EX3A10 and 4EX8K11 for ease of alignment and servicing. The Test Set meters the oscillator, multipliers, and the regulated 10 volts.

The regulated 10 volts, oscillator keying voltage, system negative, and ground connections are supplied by the two cables from receiver plug P443.

RF AMPLIFIER (A2351)

RF Amplifier A2351 consists of two high-Q helical resonators and an RF amplifier stage. The RF signal from the antenna is coupled by RF cable W2352 to a tap on L2353/L2355. The tap is positioned to insure the proper impedance match to the antenna. RF energy is coupled through the two coils by an opening in the shield wall to RF Amplifier Q2. The coils are tuned to the incoming frequency by air trimmer capacitors C341 and C342.

The amplifier uses a Field-Effect Transistor (FET) as the active device. The FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied between the "gate" and "source" terminals. Lead identification for the FET is shown in Figure 3. The FET has voltage-controlled characteristics, and may be compared to a vacuum tube in operation (see Figure 3).

RF from the antenna is applied to the "source" terminal of FET Q2. Q2 operates as a grounded-gate amplifier. This method of operation provides a low impedance input to the amplifier. The amplifier output is taken from the "drain" terminal and coupled through three tuned circuits (L1, L6 and L7) to the input of the 1st mixer.

1ST OSCILLATOR AND MULTIPLIER

The receiver 1st oscillator operates in a Transistorized Colpitts oscillator

DUAL FRONT END ALIGNMENTS

Refer to Receiver MAINTENANCE MANUAL for Receiver IF Alignment Procedure.

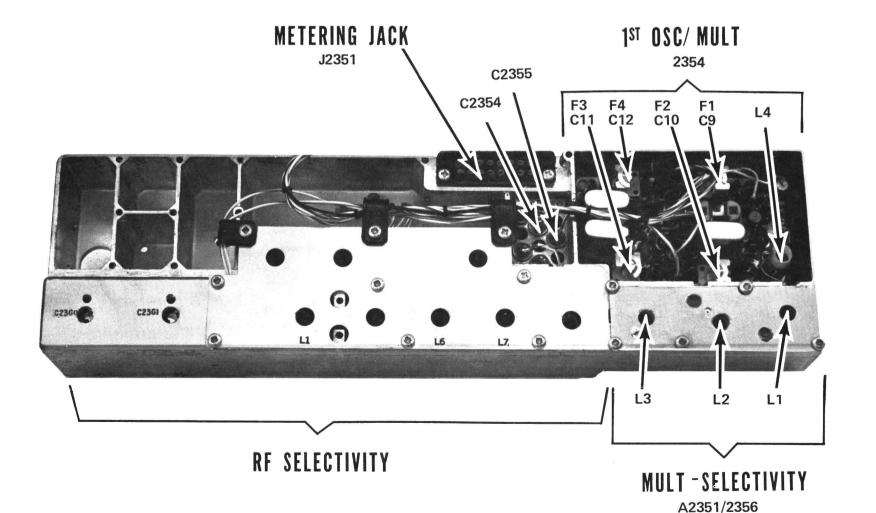
EQUIPMENT REQUIRED

- GE Test Set Models 4EX3A10 or 4EX8K11 (or a 20,000 ohm-per-volt multimeter).
- 2. Signal Generator (33-50 MHz range). Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output probe.

PRELIMINARY CHECKS AND ADJUSTMENTS

- Plug Test Set cable into metering jack J2351. With Test Set in position J, check for regulated +10 volts. If using multimeter, measure at metering jack J2351-13 and -16.
- 2. If using Multimeter for alignment, connect positive lead to J2351-16 (ground).
- 3. Set the frequency selector switch on the control unit to select the center frequency of the multi-frequency DFE.
- 4. For a large change in frequency or a badly mis-aligned DFE, set crystal trimmers C9, C10, C11 and C12 on 1st Osc/Mult board to mid-capacity.

If Receiver and Dual Front End operating frequencies are less than 1 MHz apart, connect the signal generator directly into the Dual Front End antenna connector, not into the connector.

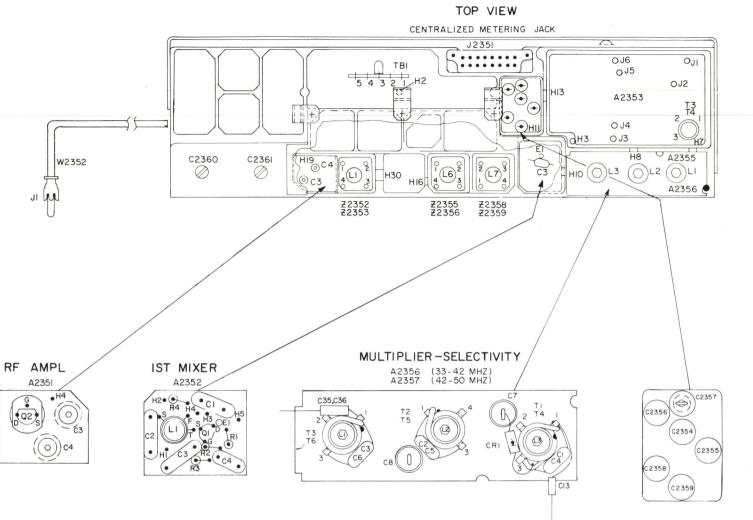


ALIGNMENT PROCEDURE

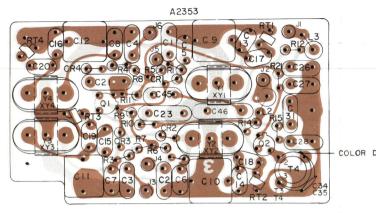
	METERING POSITION							
		Multimeter Minus at	×	METER				
STEP	GE Test Set	J2351	TUNING CONTROL	READING	PROCEDURE			
	OSCILLATOR AND MULTIPLIER							
1	D (Mult 1)	Pin 4	L4 (1st OSCILLATOR) L1 (MULT-SELECTIVITY)	Max	Tune L4 and L1 for maximum meter.			
2	D (Mult 1)	Pin 4	L2 (MULT-SELECTIVITY)	Min	Tune L2 for minimum reading. Change voltage scale if necessary.			
3	D (Mult 1)	Pin 4	L3 (MULT-SELECTIVITY)	Max	Tune L3 for maximum meter reading.			
4	D (Mult 1)	Pin 4	See Procedure		Repeat Steps 1 and 2 to assure maximum injection voltage.			
			RF CIRC	UITS				
5	A (Receiver Disc)	Pin 10		Zero	Connect Test Set to Receiver metering jack J442. Insert signal generator probe into L6 hole, and adjust Signal Generator for discriminator zero.			
6	B (2nd IF Amp on Receiver)	Pin 2	L7, L6	Max	Tune L7 for maximum meter reading. Insert generator probe in L1 hole and tune L6 for maximum meter reading.			
7	B (2nd IF Amp on Receiver)		C2360, C2361, L1 (RF AMP)	Max	Connect generator to the DFE antenna jack and tune C2360, C2361 and L1 for maximum meter reading. Reduce signal to keep reading below 0.5 volts.			
8	B (2nd IF Amp on Receiver)		L1, (RF AMP L6, L7	Max	Retune L1, L6 and L7 for maximum meter reading.			
9	B (2nd IF Amp on Receiver)	Pin 2	L4 (1st OSCILLATOR) L1, L2, L3 (MULT- SELECTIVITY)	Max	Retune L4, L1, L2 and L3 for maximum meter reading.			
10	B (2nd IF Amp on Receiver)		C2360, C2361		Retune C2360 and C2361 for maximum quieting.			
			FREQUENCY AD	JUSTMENT				
11	A (Receiver Disc)	Pin 10	C9 (on 1st OSC/MULT) (C10, C11, or C12 for multi-frequency)	Zero	Apply an on-frequency signal to the DFE Antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required. NOTE For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperature range of 50°			

ALIGNMENT PROCEDURE

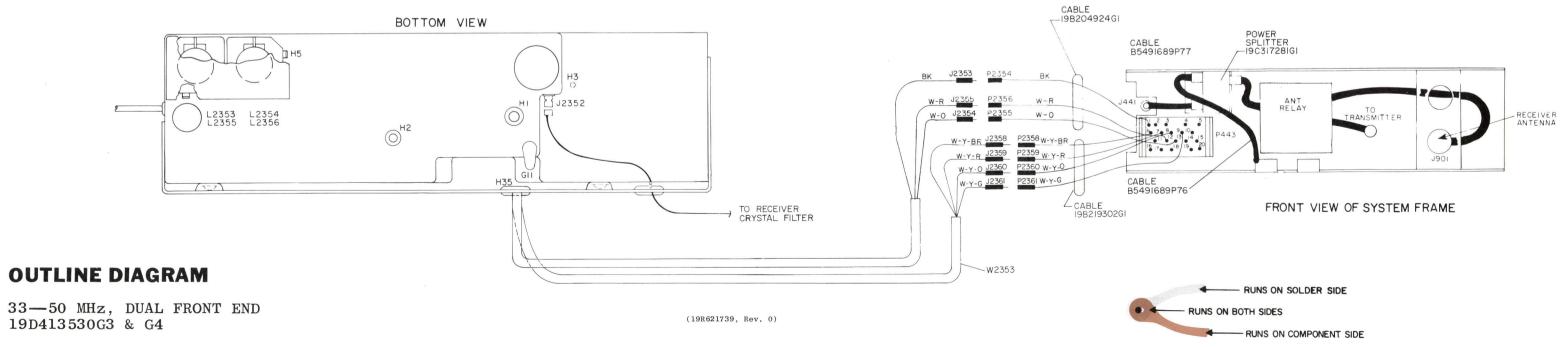
33-50 MHz, DUAL FRONT END 19D413530G3 & G4

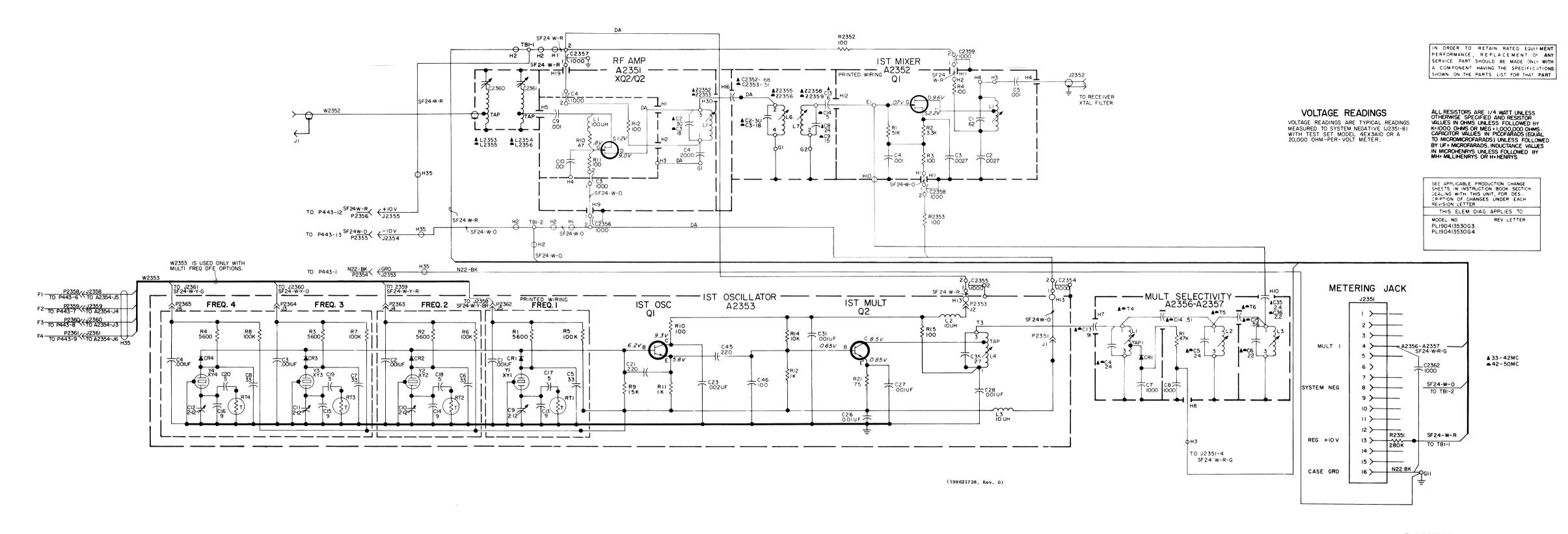






(19B204412, Sh. 1, Rev. 3) (19B204412, Sh. 2, Rev. 3)





SCHEMATIC DIAGRAM

33-50 MHz, DUAL FORNT END WITH STANDARD OSCILLATOR 19D413530G3 & G4 LBI-4243

PARTS LIST

LBI-4244A

SYMBOL	GE PART NO.	DESCRIPTION
A2351		RF AMPLIFIER 19B204772G3
C3	5493392P7	
and C4	0453352F1	Ceramic, feed-thru: .001 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type FASC.
C9 and C10	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
Ll	7491382P101	
21	7451362F101	Coil, RF: 100 mh ±10%, 4 ohms DC res max; sim to Delevan 3500 Series.
00	10411505271	TRANSISTORS
Q2	19A115953P1	N Channel; sim to TIS34.
R10	3R152P470J	RESISTORS
R11 and	3R152P101J	Composition: 100 ohms ±5%, 1/4 w.
R12		
XQ2	5490277Pl	Transistor: 4 contacts rated at 1 amp at 400
40050		VRMS; sim to Elco 3303.
A2352		FIRST MIXER 19B216867G1
		CAPACITORS
C1	5496219P258	Ceramic disc: 62 pf ±5%, 500 VDCW, temp coef -80 PPM.
C2 and C3	5494481P27	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C4	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C5	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
Ll	19B216880G1	Coil.
		RESISTORS
R1	3R152P513J	Composition: 51,000 ohms ±5%, 1/4 w.
R2	3R152P332K	Composition: 3300 ohms ±10%, 1/4 w.
R3 and R4	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.
		TRANSISTORS
Q1	19A115953P1	N Channel; sim to T1S34.
A2354		FIRST OSCILLATOR 19B204419G18
Cl thru C4	5494481P112	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C5 thru C8	5496219P751	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.

### STACE freq needed. 33-42 MHz crystal freq = (OF +5.30 MHz) : 3. 42-50 MHz crystal freq = (OF -5.30 MHz) : 4. 40-40 MHz crystal freq = (OF -5.30 MHz) : 4. 40-40 MHz crystal freq = (OF -5.30 MHz crystal freq = (OF -5.30 MHz crystal freq = (OF -5.30 MHz) : 4. 40-40 MHz crystal freq = (OF -5.30 MHz crystal fr	SYMBOL	GE PART NO.	DESCRIPTION
### STACE freq needed. 33-42 MHz crystal freq = (OF +5.30 MHz) : 3. 42-50 MHz crystal freq = (OF -5.30 MHz) : 3.			
198206576P2 Quartz: freq range 12765.66 Coff. 5.30 MHz.) 1.3 3.42 MHz. 1.70 1.35			When reordering give GE Part No. and specify exact freq needed.
198206576P2			33-42 MHz crystal freq = (OF +5.30 MHz) : 3.
thru Y4 Y1 thru Y4 12336 and A2357 C4 5496218P248 C5 5496218P248 C6 5496218P247 C7 and 5493392P107 A236 5491601P137 C14 5491601P114 C15 5491601P126 C36 5491601P127 C37 5493058P61 C37 5493058P61 C38 5491601P127 C39 5491601P126 C70 5491601P127 C39 5491601P127 C39 5491601P127 C39 5491601P126 C5 5491601P126 C6 5496218P247 C6 5496218P248 C6 5496218P247 C7 and 5491601P116 C15 5491601P116 C16 5491601P17 C17 Tubular: 0.51 pf f5%, 500 VDCW. C7 Tubular: 0.56 pf f5%, 500 VDCW. C81			•
temp range -30°C to +85°C. (42-54 MHz). 22356 and A2357 19820532567 A2357 19820532567 A2357 19820532567 A2357 19820532568 A2357 19820532562 A2358 A23	thru	19B206576P2	Quartz: freq range 12766.667 to 15766.666 K temp range -30°C to +85°C. (33-42 MHz).
A2356 189205325G7 A2357 198205325G7 A2357 198205325G7 A2357 198205325G7 C6 5496218P248	thru	19B206576P3	Quartz: freq range 12233.333 to 16233.333 K temp range -30°C to +85°C. (42-54 MHz).
C4 and C5 C6 5496218P247 C6 5496218P247 C7 and C1sc: 22 pf f5%, 500 VDCW, temp coe-80 PPM. C7 and C8 C13 549393P107 C14 5491601P117 C15 5491601P115 C35 5491601P126 C8	and		A2356 19B205326G7
-80 PPM. C6 5496218P247 Ceramic disc: 22 pf ±5%, 500 VDCW, temp coe-80 PPM. C7 and c8 C13 5491601P137 Tubular: 0.91 pf ±5%, 500 VDCW. C14 5491601P114 Tubular: 0.51 pf ±5%, 500 VDCW. C15 5491601P127 Phenolic: 2.4 pf ±5%, 500 VDCW. C35 5491601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. C81 4038056P1 Germanium. C81 4038056P1 Germanium. C81 4038056P1 Composition: 47,000 ohms ±10%, 1/4 w. C81 198205325G2 Coll. Tubular: 0.68 pf ±5%, 500 VDCW. T4 198205325G1 Coll. Tubular: 0.68 pf ±5%, 500 VDCW. C2352 5491601P117 Tubular: 0.68 pf ±5%, 500 VDCW. C2353 5491601P114 Tubular: 0.68 pf ±5%, 500 VDCW. C2353 5491601P117 Tubular: 0.68 pf ±5%, 500 VDCW. C2354 Ceramic feed-thru: 0.01 pf ±100% -0%, 500 VDCW. C2355 198205889C2 Ceramic feed-thru: 0.01 pf ±100% -0%, 500 VDCW. C2356 5494481P12 Ceramic disc: .001 pf ±10%, 1000 VDCW; sim thru L2356 L2353 Thru L2353 198205689C2 Connector: 18 contacts rated at 5 amps min 1000 VDC max. C001 ASSEMBLY, C011 ASSEMBLY, C012 ASSEMBLY, C2356 L2356 198204820C3 L2356 198204820C4			
S493392P107	and	5496218P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coe -80 PPM.
Tubular: 0.91 pf ±5%, 500 VDCW. C14 5491601P137 Tubular: 0.51 pf ±5%, 500 VDCW. C15 5491601P127 Phenolic: 2.4 pf ±5%, 500 VDCW. C35 5491601P127 Phenolic: 2.2 pf ±5%, 500 VDCW. C36 5491601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. CR1 4038056P1 Germanium.	C6	5496218P247	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coe -80 PPM.
C14 5491601P114 Tubular: 0.51 pf ±5%, 500 VDCW. C15 5491601P127 Phenolic: 2.4 pf ±5%, 500 VDCW. C36 5491601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. C36 5491601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. C37 C38 5491601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. C38 C39 C391601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. C39 C39 C391601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. C4 C39 C5491601P14 C5491798P4 C611. C5491798P4 Tuning slug. C55 C611. C5491798P4 Tuning slug. C55 C611. C5491798P4 Tuning slug. C5352 5491601P117 Tubular: 0.68 pf ±5%, 500 VDCW. C5353 5491601P114 Tubular: 0.51 pf ±5%, 500 VDCW. C5354 Turing slug. C5354 C5493392P7 Ceramic feed-thru: .001 pf +100% -0%, 500 V sim to Allen-Bradley Type FASC. C5362 5494481P12 Ceramic disc: .001 pf ±10%, 1000 VDCW; sim RMC Type JF Discap. C5353 T147199P1 Connector: 18 contacts rated at 5 amps min 1000 VDC max. C5353 T147199P1 Connector: coaxial: sim to Micon Electronic Inc Type 1104. C5353 19820482033 L2356 19820482033 L2356 19820482033 L2356 19820482033 L2356 19820482033 L2356 19820482033 L2356 19820482034 L235	and	5493392P107	Ceramic feed-thru: 470 pf +100% - 0%, 500 W
C15 5491601P115 Tubular: 0.56 pf ±5%, 500 VDCW. C36 5491601P127 Phenolic: 2.4 pf ±5%, 500 VDCW. C36 5491601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. DIODES AND RECTIFIERS Germanium. RESISTGRS C38 19820532502 Coil. T4 19820532501 Coil. T5 19820532501 Tuning slug. C2352 5491601P117 Tubular: 0.68 pf ±5%, 500 VDCW. C2353 5491601P114 Tubular: 0.51 pf ±5%, 500 VDCW. C2354 5493392P7 Ceramic feed-thru: .001 pf +100% -0%, 500 V sim to Allen-Bradley Type FASC. C2362 5494481P12 Connector: 18 contacts rated at 5 amps min 1000 VDC max. J2351 19820568962 Connector: 18 contacts rated at 5 amps min 1000 VDC max. C3553 Thru L2355 19820482003 L2356	C13	5491601P137	Tubular: 0.91 pf ±5%, 500 VDCW.
C35	C14	5491601P114	Tubular: 0.51 pf ±5%, 500 VDCW.
C36 5491601P126 Phenolic: 2.2 pf ±5%, 500 VDCW. DIODES AND RECTIFIERS	C15	5491601P115	Tubular: 0.56 pf ±5%, 500 VDCW.
CR1 4038056P1 Germanium.	C35	5491601P127	Phenolic: 2.4 pf ±5%, 500 VDCW.
CR1	C36	5491601P126	Phenolic: 2.2 pf ±5%, 500 VDCW.
R1 3R152P473K Composition: 47,000 ohms ±10%, 1/4 w.	CR1	4038056Pl	i
T4			
T4	R1	3R152P473K	Composition: 47,000 ohms $\pm 10\%$, $1/4$ w.
L1 5491798P4 Tuning slug. T5 and T6 L2 and L3	m.4	10000520500	
and T6 1.2 and L3			
L2 and L3	and	19B205325G1	Coil.
C2352 5491601P117 Tubular: 0.68 pf ±5%, 500 VDCW. C2353 5491601P114 Tubular: 0.51 pf ±5%, 500 VDCW. C2354 thru C2359 5493392P7 Ceramic feed-thru: .001 pf ±100% -0%, 500 Vocuments of the case of th	L2 and	5491798P4	Tuning slug.
C2353 5491601P114 Tubular: 0.51 pf ±5%, 500 VDCW. C2354 thru C2359 Ceramic feed-thru: .001 pf +100% -0%, 500 V sim to Allen-Bradley Type FA5C. C2362 5494481P12 Ceramic disc: .001 pf ±10%, 1000 VDCW; sim RMC Type JF Discap. JACKS AND RECEPTACLES J2351 19820568962 Connector: 18 contacts rated at 5 amps min 1000 VDC max. J2352 19A115465P1 Connector, coaxial: sim to Micon Electronic Inc Type 1104. J2353 thru J2356 CONNECTOR: male contact; sim to Winchester Electronics 21803. INDUCTORS CONNECTOR: male contact; sim to Winchester Electronics 21803. COIL ASSEMBLY L2353 19B204820G1 L2354 19B204820G3 L2356 19B204820G3 L2356 19B204820G4			
C2354 thru c2359 C2362 5494481P12 Ceramic feed-thru: .001 pf +100% -0%, 500 V sim to Allen-Bradley Type FA5C. C2362 5494481P12 Ceramic disc: .001 pf ±10%, 1000 VDCW; sim RMC Type JF Discap. JACKS AND RECEPTACLES J2351 198205689G2 Connector: 18 contacts rated at 5 amps min 1000 VDC max. Connector: 18 contacts rated at 5 amps min 1000 VDC max. J2352 19A115465P1 Connector: coaxial: sim to Micon Electronic Inc Type 1104. Connector: male contact; sim to Winchester Electronics 21803.	C2352	5491601P117	Tubular: 0.68 pf ±5%, 500 VDCW.
Sim to Allen-Bradley Type FA5C. Sim to Allen-Bradley Type FA5C.	C2353		Tubular: 0.51 pf ±5%, 500 VDCW.
RMC Type JF Discap. JACKS AND RECEPTACLES Connector: 18 contacts rated at 5 amps min 1000 VDC max. J2352 19Al15465P1 Connector, coaxial: sim to Micon Electronic Inc Type 1104. Connector: male contact; sim to Winchester Electronics 21803. INDUCTORS COLL ASSEMBLY L2353 19B204820G1 L2354 19B204820G2 L2355 19B204820G3 L2356 19B204820G4 CAPACITORS Variable, subminiature: approx 1,70-6.9 pf, and 750 v peak; sim to EF Johnson 189.	thru	5493392P7	Ceramic feed-thru: .001 pf +100% -0%, 500 V sim to Allen-Bradley Type FA5C.
J2351 19B205689G2 Connector: 18 contacts rated at 5 amps min 1000 VDC max. J2352 19A115465P1 Connector, coaxial: sim to Micon Electronic Inc Type 1104. J2353 thru J2356 COIL ASSEMBLY L2356 COIL ASSEMBLY L2354 19B204820G1 L2355 19B204820G2 L2355 19B204820G3 L2356 19B204820G4	C2362	5494481P12	Ceramic disc: .001 pf ±10%, 1000 VDCW; sim RMC Type JF Discap.
J2352 19All5465Pl Connector, coaxial: sim to Micon Electronic Inc Type 1104. J2353 7147199Pl Connector: male contact; sim to Winchester Electronics 21803. COIL ASSEMBLY L2353 19B204820G2 L2355 19B204820G2 L2355 19B204820G3 L2356 19B204820G4			JACKS AND RECEPTACLES
J2353 thru J2356 Connector: male contact; sim to Winchester Electronics 21803. COIL ASSEMBLY L2353 thru L2356 COIL ASSEMBLY L2353 198204820G1 L2354 198204820G2 L2355 198204820G3 L2356 198204820G4	J2351	19B205689G2	Connector: 18 contacts rated at 5 amps min 1000 VDC max.
thru J2356 L2353 thru L2356 COIL ASSEMBLY L2353 19B204820G1 L2354 19B204820G2 L2355 19B204820G3 L2356 19B204820G4			Connector, coaxial: sim to Micon Electronic Inc Type 1104.
L2353 thru L2356 L2356 L2357 L2358 L2356 L	thru	7147199P1	
L2353 198204820G1 L2356 L2351 198204820G2 L2355 198204820G3 L2356 198204820G4			
C2361 19B209159P3 Variable, subminiature: approx 1.70-6.9 pf, and 750 v peak; sim to EF Johnson 189.	thru		L2353 19B204820G1 L2354 19B204820G2 L2355 19B204820G3
and 750 v peak; sim to EF Johnson 189.			CAPACITORS
	and	19B209159P3	Variable, subminiature: approx 1.70-6.9 pf, 750 v peak; sim to EF Johnson 189.

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PAR
		INDICATING DEVICES		
DS301	19B209067P1	Lamp, glow: 0.3 ma; sim to GE NE-2T.		7162414
				19B2049
P2351	4029840P2	Contact, electrical; sim to Amp 42827-2.		4033089
thru P2353				19B2005
	:	RESISTORS		19A1157
R2351	19A116278P444	Metal film: 0.28 megohm ±2%, 1/2 w.		4039307
R2352 and R2353	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.		
		TERMINAL BOARDS		
TB1	7487424P7	Miniature, phen: 4 terminals.		
W2352	19A122563G2	Cable, RF: approx 31 inches long.		
W2353	19B219304G1	Cable, RF: approx 15-1/4 inches long.		
		TUNED CIRCUITS		
Z2352 and		COIL ASSEMBLY		
Z2353		Z2352 19B204786G5 Z2353 19B204786G6		
Cl	5496218P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef -80 PPM.		
C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.		
сз	5496218 P2 45	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef		
C4	5494481P14	-80 PPM. Ceramic disc: .002 pf ±10%, 500 VDCW; sim to		
		RMC Type JF Discap.		
		MISCELLANEOUS		
	5491798P1	Tuning slug. (Used in Z2352).		
	5491798P4	Tuning slug. (Used in Z2353).		
Z2355 and		COIL ASSEMBLY 22355 19B204767G2		
Z2356		Z2356 19B204767G3		
		CAPACITORS		
C1	5496218P254	Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef -80 PPM.		
C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.		
СЗ	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.		
		·		
	540170 en 1	MISCELLANEOUS		
	5491798P1 5491798P4	Tuning slug. (Used in Z2355). Tuning slug. (Used in Z2356).		
70250	· *			
Z2358 and Z2359		COIL ASSEMBLY 22358 19B204784G9 22359 19B204784G10		
C7	5496218P248			
		-80 PPM.		
C9	5496218P244	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -80 PPM.		
C13	5496218P237	Ceramic disc: 6.0 pf ±5%, 500 VDCW, temp coef -80 PPM.		
C14	5496218P236	Ceramic disc: 5.0 pf ±5%, 500 VDCW, temp coef -80 PPM.		
		miscellaneous		
	5491798P1	Tuning slug. (Used in Z2358).		
	5491798P4	Tuning slug. (Used in Z2359).		
			1 1	

ART NO. DESCRIPTION GE PART NO. DESCRIPTION SYMBOL ----- MISCELLANEOUS -----C9 thru C12 5491271P106 Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189. 14P1 Transistor, socket. (Used with Q2 in A2351). 4917P1 Support. (Used with Q2 in A2351). C13 thru C16 5496219P40 Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM. Rivet (Part of XY1). C17 thru C20 19C300685P93 Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp coe 5793P1 Contact (Part of XY1). Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -750 PPM. Crystal socket (Part of XY1). C21 5496219P771 C23 5494481P114 Ceramic disc: .002 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap. 5494481P112 Ceramic disc: .001 pf \pm 10%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: .001 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap. C31 5494481P112 C45 Silver mica: 220 pf ±5%, 500 VDCW. 5490008P35 Ceramic disc: 100 pf $\pm 5\%$, 500 VDCW, temp coef -330 PPM. C46 5496219**P**563 - - - - - - DIODES AND RECTIFIERS - - - - -CR1 thru CR4 19A115603P1 - - - - - JACKS AND RECEPTACLES - - - - -4033513P4 Contact, electrical: sim to Bead Chain L93-3. - - - - - - - INDUCTORS - - - - - - -7488079**P**16 Choke, RF: 10 µh ±10% ind at 640 ma, 0.6 ohm DC res; sim to Jeffers 4421-7K. - - - - - - - TRANSISTORS - - - - - -19A115330Pl Silicon, NPN. ----- RESISTORS -----3R152P562J Composition: 5600 ohms ±5%, 1/4 w. R5 thru R8 3R152P104K Composition: 0.10 megohm ±10%, 1/4 w. 3R152P153J R9 Composition: 15,000 ohms ±5%, 1/4 w. R10 3R152P101K Composition: 100 ohms ±10%, 1/4 w. R11 and R12 3R152P102J Composition: 1000 ohms ±5%, 1/4 w. R14 3R152P103J Composition: 10,000 ohms ±5%, 1/4 w. R15 3R152P101K R21 3R152P750J Composition: 75 ohms ±5%, 1/4 w. RT1 thru RT4 19B209284P5 Disc: 43 ohms res nominal at 25°C, color code T4 COIL ASSEMBLY 19B205416G2 Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM. 5496218P253 C34 5496218P249 Ceramic disc: 27 pf $\pm 5\%$, 500 VDCW, temp coef -80 PPM. - - - - - - - - SOCKETS - - - - - -Refer to Miscellaneous, *COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

SCHEMATIC DIAGRAM

33-50 MHz, DUAL FORNT END WITH STANDARD OSCILLATOR 19D413530G3 & G4 LBI-4243

PARTS LIST

LBI-4244B

DUAL FRONT END 33-50 MHz 19D413530G3 33-42 MHz 19D413530G4 42-50 MHz

SYMBOL	GE PART NO.	DESCRIPTION
A2351		RF AMPLIFIER 19B204772G3
C3 and C4	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW sim to Allen-Bradley Type FASC.
C9 and C10	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
Ll	7491382P101	Coil, RF: 100 µh ±10%, 4 ohms DC res max; sim to Delevan 3500 Series.
		TRANSISTORS
Q2*	19A116960P1	N Type, field effect; sim to Type 2N4416.
		Earlier than REV A:
	19A115953P1	N Channel; sim to T1S34.
		RESISTORS
R10	3R152P470J	Composition: 47 ohms ±5%, 1/4 w.
R11 and R12	3R152P101J	Composition: 100 ohms ±5%, 1/4 w.
	1	SOCKETS
XQ2	5490277P5	Transistor: 3 contacts rated at 1 amp at 400 VRMS; sim to Alcon 1213LL2.
A2352		FIRST MIXER 19B216867G1
Cl	5496218P258	Ceramic disc: 62 pf ±5%, 500 VDCW, temp coef -80 PPM.
C2 and C3	5494481P127	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C4	5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C5	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
Ll	19B216880G1	Coil.
Q1 *	19A116960P1	N Type, field effect; sim to Type 2N4416.
		Earlier than REV A:
	19A115953P1	N Type, field effect.
R1	3R152P513J	Composition: 51,000 ohms ±5%, 1/4 w.
R2 R3	3R152P332K 3R152P101K	Composition: 3300 ohms ±10%, 1/4 w. Composition: 100 ohms ±10%, 1/4 w.
and R4	JRIJEFIOIR	Composition. 100 times 110, 1/4 v.

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

					Г	г
SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	
A2353		FIRST OSCILLATOR 19B204419G18	XY1 thru		SOCKETS	1
Cl thru	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	XY4			
C4 C5 thru	5496219P751	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.			NOTE: When reordering give GE Part No. and specify exact freq needed.	
C8 C9 thru	5491271P106	Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.			33-42 MHz crystal freq = (<u>OF +5.30 MHz</u>) 3 42-50 MHz crystal freq = (<u>OF -5.30 MHz</u>)	
C12 C13 thru	5496219P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.	Y1 thru Y4	19B206576P2	Quartz: freq range 12766.667 to 15766.666 KHz, temp range -30°C to +85°C. (33-42 MHz).	
C16 C17 thru	19C300685P93	Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp coef 0 PPM.	Y1 thru Y4	19B206576P3	Quartz: freq range 12233.333 to 16233.333 KHz, temp range -30°C to +85°C. (42-54 MHz).	
C20 C21	5496219P771	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -750 PPM.	A2356		MULTIPLIER SELECTIVITY ASSEMBLY A2356 19B205326G7	
C23	5494481P114	Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	A2357		A2357 19B205326G8	
C26 thru C28	5494481P112	Ceramic disc: 1000 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.	C4 and	5496218P248		
C31	5494481P112	Ceramic disc: 1000 pf \pm 10%, 1000 VDCW; sim to RMC Type JF Discap.	C5 C6	5496218P247	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef	
C45	5490008P35	Silver mica: 220 pf ±5%, 500 VDCW.		5493392P107	-80 PPM. Ceramic feed-thru: 470 pf +100% - 0%, 500 VDCW.	
C46	5496219P563	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef -330 PPM.	C7 and C8	54933929107	Ceramic leed-thid. The pr 4100% - 0%, 000 visco.	
		DIODES AND RECTIFIERS	C13	5491601P137	Phenolic: 0.91 pf ±5%, 500 VDCW.	
CR1 thru	19A115603P1	Silicon.	C14	5491601P114	Phenolic: 0.51 pf ±5%, 500 VDCW. Phenolic: 0.56 pf ±5%, 500 VDCW.	П
CR4		JACKS AND RECEPTACLES	C15 C35	5491601P115 5491601P127	Phenolic: 2.4 pf ±5%, 500 VDCW.	Ш
J1 thru J6	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	C36	5491601P126	Phenolic: 2.2 pf ±5%, 500 VDCW.	
		INDUCTORS	CR1	4038056P1	DIODES AND RECTIFIERS	П
L1 and L2	7488079P16	Choke, RF: 10 μh $\pm 10\%$ ind at 640 ma, 0.6 ohm DC res; sim to Jeffers 4421-7K.		3R152P473K	RESISTORS	
		TRANSISTORS	R1	3R152P473R	Composition: 47,000 ohms ±10%, 1/4 w.	Ш
Q1 and Q2	19A115330P1	Silicon, NPN.	T4 L1	19B205325G2 5491798P4	TRANSFORMERS	
		RESISTORS	Т5	19B205325G1	Coil.	Ш
R1 thru R4	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	and T6 L2 and	5491798P4	Tuning slug.	
R5 thru R8	3R152P104K	Composition: 0.10 megohm ±10%, 1/4 w.	L3			
R9	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	C2352	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.	
R10	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	C2353	5491601P114	Phenolic: 0.51 pf ±5%, 500 VDCW.	11
Rll and Rl2	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	C2354 thru C2359	5493392P7	Ceramic feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.	
R14	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	C2362	5494481P12	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	$\ \cdot \ $
R15	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.			JACKS AND RECEPTACLES	
R21	3R152P750J	Composition: 75 ohms ±5%, 1/4 w.	J2351	19B205689G2	Connector: 18 contacts rated at 5 amps min at 1000 VDC max.	
RT1 thru	19B209284P5	Disc: 43 ohms res nominal at 25°C, color code green.	J2352	19A115465P1	Connector, coaxial: sim to Micon Electronics Inc. Type 1104.	
RT4		TRANSFORMERS	J2353 thru J2355	7147199Pl	Connector: male contact; sim to Winchester Electronics 21803.	
Т3		COIL ASSEMBLY 19B205416G2	1 2233			
025	5496218P249		L2353 thru L2355		COIL ASSEMBLY L2353 19B204820G1 L2354 19B204820G2 L2355 19B204820G3	
C35		-80 PPM.				
1.4	19A121464P2 5491798P5	Coil. Tuning slug.	C2360 and	19B209159P3	CAPACITORS Variable, subminiature: approx 1.70-6.9 pf, 750 v peak; sim to EF Johnson 189.	

SYMBOL	GE PART NO.	DESCRIPTION	SYMB
L2356		COIL ASSEMBLY	С9
		19B204820G4	C13
		CAPACITORS	1
C2361*	19B209159P4	Variable, air, sub-miniature: 1.80-8.30 pf, 650 v peak; sim to EF Johnson 189. In 19D413530G4 of REV A and earlier:	C14
	19B209159P3	Variable, air, sub-miniature: 1.70-6.90 pf,	
		750 v peak; sim to EF Johnson 189.	1
		INDICATING DEVICES	
DS301	19B209067P1	Lamp, glow: 0.3 ma; sim to GE NE-2T.	1
		PLUGS	1
P2351	4029840P2	Contact, electrical; sim to Amp 42827-2.	
thru P2353			
		RESISTORS	
R2351	19A116278P444	Metal film: 0.28 megohm ±2%, 1/2 w.	
R2352 and	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	
R2353		TERM INAL BOARDS	
TB1	7487424P7	Miniature, phen: 4 terminals.	
W2352	19A122563G2	Cable, RF: approx 31 inches long.	
W2352	19B219304G1	Cable, RF: approx 15-1/4 inches long.	
		TUNED CIRCUITS	
Z2352 and Z2353		COIL ASSEMBLY 22352 198204786G5 22353 198204786G6	
C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	
СЗ	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	
C4	5494481P14	Ceramic disc: 2000 pf ±10%, 500 VDCW; sim to RMC Type JF Discap.	
Ll	19B204786P10	Coil.	
ш	198204780910		
		MISCELLANEOUS	
	5491798P4	Tuning slug. (Used in Z2352).	
	5491798P5	Tuning slug. (Used in Z2353).	
Z23 55 and Z2356		COIL ASSEMBLY 22355 19B204767G2 22356 19B204767G3	
C2	5496218P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	
СЗ	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	
		MISCELLANEOUS	
	5491798P4	Tuning slug. (Used in Z2355).	
	5491798P5	Tuning slug. (Used in Z2356).	
Z2358 and Z2359		COIL ASSEMBLY 22358 19B204784G9 22359 19B204784G10	
C7	5496218P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.	

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
L2356		COIL ASSEMBLY 19B204820G4	C9	5496218P244 5496218P237	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -80 PPM. Ceramic disc: 6.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
C2361*	19B209159P4	Variable, air, sub-miniature: 1.80-8.30 pf, 650 v peak; sim to EF Johnson 189. In 19D413530G4 of REV A and earlier:	C14	5496218P236	Ceramic disc: 5.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
	19B209159P3	Variable, air, sub-miniature: 1.70-6.90 pf, 750 v peak; sim to EF Johnson 189.		5491798P4 5491798P5	Tuning slug. (Used in Z2358). Tuning slug. (Used in Z2359).
DS301	19B209067P1	INDICATING DEVICES Lamp, glow: 0.3 ma; sim to GE NE-2T.		7162414P1 19B204917P1	Transistor, socket. (Used with Q2 in A2351). Support. (Used with Q2 in A2351).
P2351 thru P2353	4029840P2	Contact, electrical; sim to Amp 42827-2.		4033089P1 19B200525P9	Clip. (Part of XY1). Rivet. (Part of XY1).
R2351 R2352 and R2353	19A116278P444 3R152P101K	Metal film: 0.28 megohm ±2%, 1/2 w. Composition: 100 ohms ±10%, 1/4 w.		19A115793P1 4039307P1	Contact. (Part of XY1). Crystal socket. (Part of XY1).
TB1	7487424P7	Miniature, phen: 4 terminals.			
W2352 W2353	19A122563G2 19B219304G1	Cable, RF: approx 31 inches long. Cable, RF: approx 15-1/4 inches long.			
Z2352 and Z2353					
C2	5496218P250				
C3 C4	5496218P245 5494481P14	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM. Ceramic disc: 2000 pf ±10%, 500 VDCW; sim to			
		RMC Type JF Discap.			
L1	19B204786P10	Coil.			
	5491798P4 5491798P5	Tuning slug. (Used in Z2352). Tuning slug. (Used in Z2353).			
Z23 55 and Z2356		COIL ASSEMBLY 22355 19B204767G2 22356 19B204767G3			
C2	5496218P250				
С3	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.)
	5491798P4 5491798P5	Tuning slug. (Used in Z2355). Tuning slug. (Used in Z2356).			
Z2358 and Z2359		COIL ASSEMBLY Z2358 19B204784G9 Z2359 19B204784G10			
С7	5496218P248				

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

Dual Front End 19D413530G3,4

REV. A - To incorporate new transistor. Changed Q2

Dual Front End 19D413530G4

REV. B - To improve tuning range of second RF stage. Changed C2361.

ORDERING SERVICE PARTS

Each component appearing on the schematic diagram is identified by a symbol number to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and GE Part Number.

Service parts may be obtained from Authorized GE Communication Equipment Service Stations or through any GE Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

- GE Part Number of component
 Description of part
 Model number of equipment
 Revision letter stamped on unit

These instructions do not purport to cover all details or variations in equipment nor to provide for every possible contingency to be met in connection with installation, operation or maintenance.

Should further information be desired, or should particular problems arise which are not covered sufficiently for the purchaser's purposes, contact the nearest Radio Communication Equipment Sales Office of the General Electric Company.

LBI-4243

MOBILE RADIO DEPARTMENT
GENERAL ELECTRIC COMPANY • LYNCHBURG, VIRGINIA 24502

